

Let us consider a transistor having the following I/V characteristics (Figure 1)

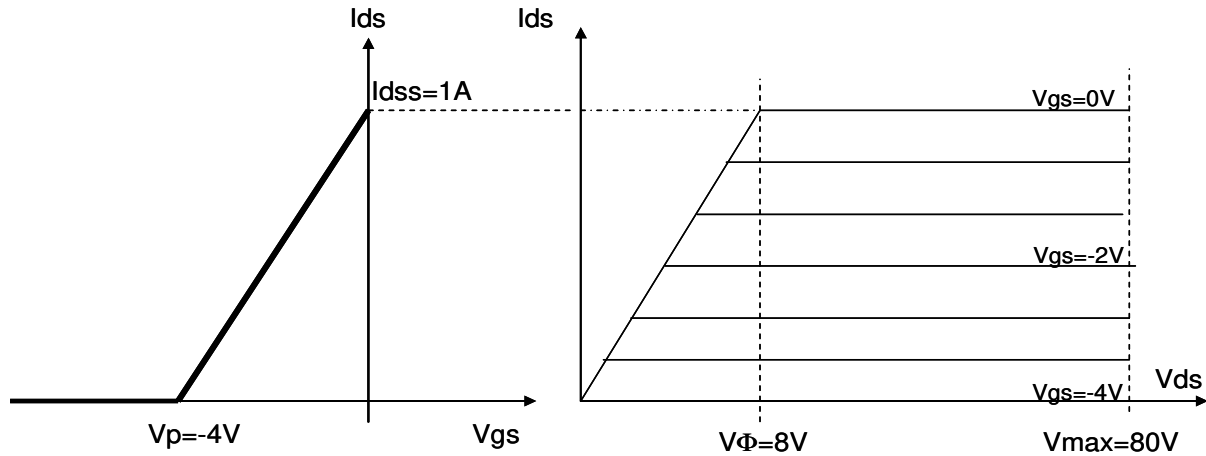


Figure 1

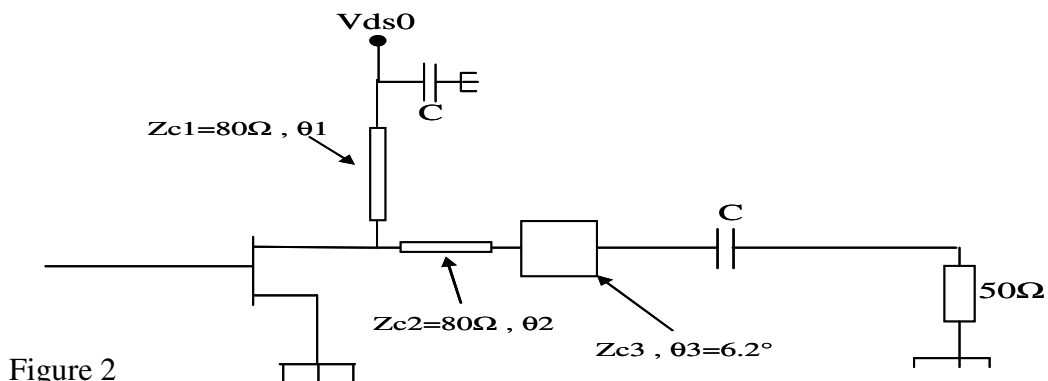
We consider also the following parameters:

$$R_g = 4\Omega, \quad C_{gs} = 5pF, \quad F_o = 3.6 \text{ GHz}, \quad C_{ds} = 0.76 pF$$

The gate source bias voltage V_{gs0} is chosen in order to have an aperture angle $\phi = 110^\circ$ when V_{gs1} is at its maximum value . ($V_{gs(t)_{max}} = 0V$)

I] In this first part we want to obtain the maximum output RF power

- 1) Determine the values of V_{gs0} and V_{ds0}
- 2) Determine the corresponding optimal load impedance (Real part and Imaginary part)
- 3) Calculate the output power and the power added efficiency
- 4) We want to design the output RF matching Network with distributed elements as represented in Figure 2



Determine the values of the electrical lengths θ_1 and θ_2 and the value of the characteristic impedance Z_{c3}

II] In this second part we keep the same values for the load impedance, V_{gs0} and V_{ds0} than the ones obtained in Part I but V_{gs1} is decreased.
 V_{gs1} is now equal to +2V.

1) What are the corresponding values of the output RF power and the PAE.

III] In this third part we keep the same values of the load impedance and V_{gs0} .
 We keep also V_{gs1} equal to +2V but we decrease the value of V_{ds0} .

1) What is the minimal value of V_{ds0} for which we reach the saturation regime of the transistor

2) What are the corresponding values of the output power and the PAE

IV] In this last part we take again the values of V_{gs0} and V_{ds0} determined in part I
 We keep $V_{gs1}=+2V$ but we modify the value of the load impedance in order to have the maximum possible output RF power for $V_{gs1}=+2V$.

1) Determine the required value of the load resistance as well as the corresponding values of the output RF power and the PAE.

I]

$$1) \begin{aligned} V_{gs0} - V_{gs0} \cos \varphi &= V_p & V_{gs1} &= -V_{gs0} = |V_{gs0}| \\ V_{gs0} &= \frac{V_p}{1 - \cos \varphi} = 3V & \rightarrow V_{gs1} &= +3V \end{aligned} \quad \begin{aligned} V_{ds0} &= \frac{80+8}{2} = 44V \\ V_{ds1} &= 44-8 = 36V \end{aligned}$$

$$2) \begin{aligned} I_{ds0} &= \frac{I_p}{\pi} \frac{\sin \varphi - \varphi \cos \varphi}{1 - \cos \varphi} = 378 \text{ mA} \quad (I_p = 1A) \\ I_{ds1} &= \frac{I_p}{\pi} \frac{\varphi - \sin \varphi \cos \varphi}{1 - \cos \varphi} = 532 \text{ mA} \end{aligned} \quad R_{opt} = \frac{V_{ds1}}{I_{ds1}} = \frac{36}{0.532} = 68 \Omega$$

$$Y_{opt} = \frac{1}{R_{opt}} + \frac{1}{jL\omega} \quad \text{with } LC\omega^2 = 1 \rightarrow \frac{1}{jL\omega} = -jC\omega$$

$$Y_{opt} = \frac{1}{R_{opt}} - jC\omega = (14.8 - j17.2) \text{ mS} \rightarrow Z_{opt} = \frac{1}{Y_{opt}} = (28.7 + j33.4) \Omega$$

$$Y_{opt} \approx (29 + j33) \Omega$$

$$3) \begin{aligned} P_{out} &= \frac{1}{2} V_{ds1} I_{ds1} = 9576 \text{ mW} \\ g_{in} &= R_g C_{gs}^2 \omega^2 = 51 \text{ mS} & P_{in} &= \frac{1}{2} g_{in} (V_{gs1})^2 = 230 \text{ mW} \\ PAE &= \frac{9576 - 230}{44 \times 378} = 56.2\% \end{aligned}$$

4) $\theta_1 = 90^\circ$ (corresponding to a $\lambda/4$ line)

For the output RF matching we want to have the following equivalence

Network

68Ω \rightarrow L \rightarrow $C = C_{ds}$ \rightarrow 50Ω

\Leftrightarrow

68Ω \rightarrow $Z_c, \lambda/4$ \rightarrow 50Ω

$\Rightarrow Z_c = 58 \Omega$

The chain matrix of the C, L, C network is

$$\begin{pmatrix} 1 - L C d s \omega^2 & j L \omega \\ j C d s \omega + j C d s \omega (1 - L C d s \omega^2) & 1 - L C d s \omega^2 \end{pmatrix} = \begin{pmatrix} 0 & j Z_c \\ j / Z_c & 0 \end{pmatrix}$$

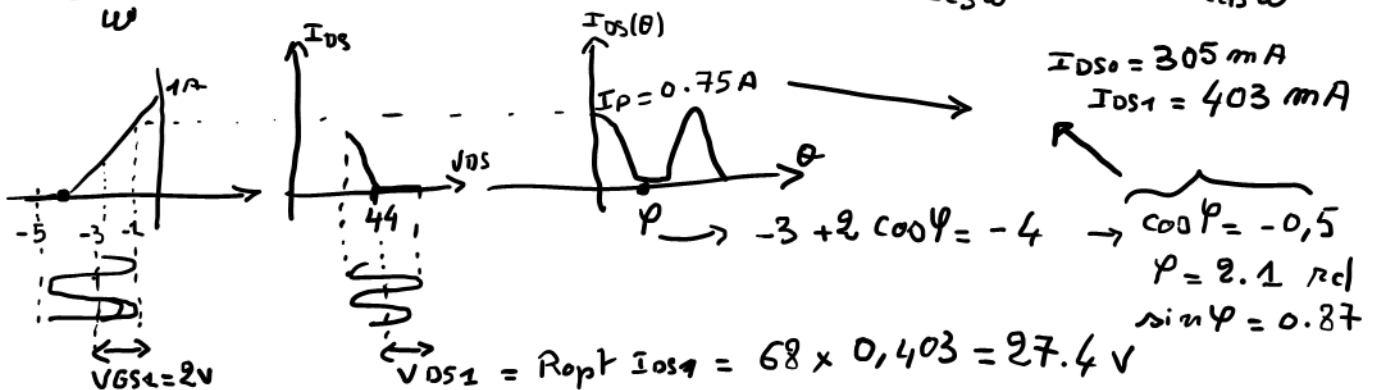
$$\rightarrow L C d s \omega^2 = 1 \rightarrow L = 2.57 \text{ mH}$$

$$\frac{1}{C d s \omega} = Z_c \rightarrow \text{OK } Z_c = 58 \Omega$$

$$L = \frac{Z_{c2} \theta_2}{\omega} \rightarrow \theta_2 = 0.727 \text{ rad}$$

$$C = C_{ds} = \frac{\theta_3}{Z_{c3} \omega} \rightarrow Z_{c3} = \frac{\theta_3}{C d s \omega} = 6 \Omega$$

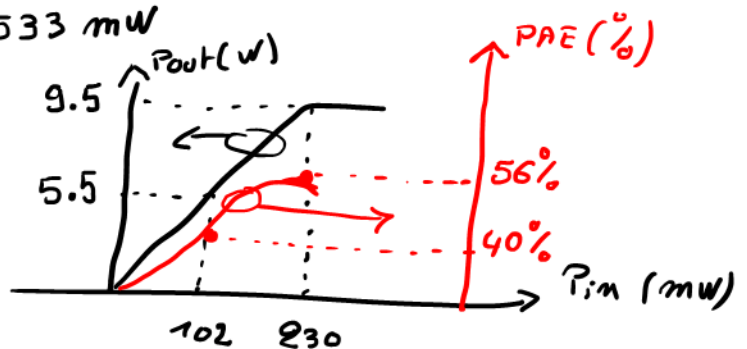
II



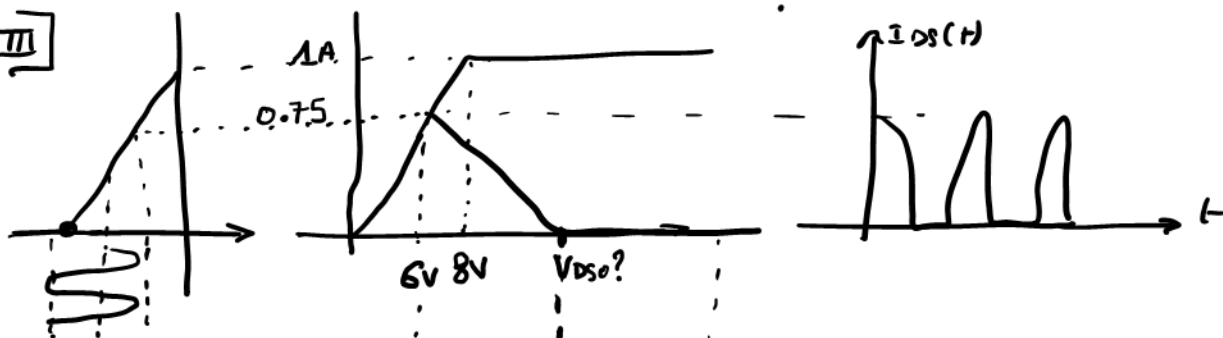
$$P_{in} = \frac{1}{2} g_{in} V_{gs1}^2 = \frac{1}{2} \times 51 \times 10^{-3} \times (2)^2 = 102 \text{ mW}$$

$$P_{out} = \frac{1}{2} V_{DS1} \cdot I_{DS1} = \frac{1}{2} R_{opt} I_{DS1}^2 = 5533 \text{ mW}$$

$$PAE = \frac{5533 - 102}{44 \times 305} = 40.4\%$$



III

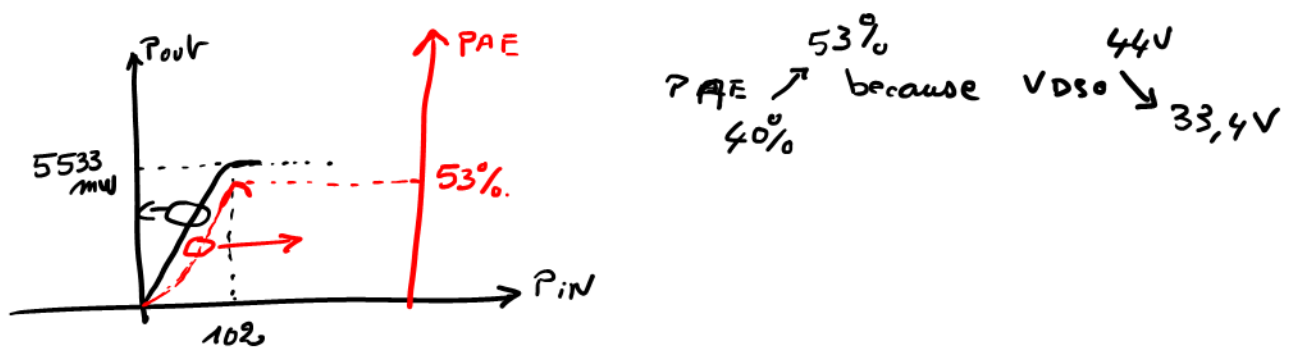


$$S_0: V_{DS0_{min}} = 6V + 27.4V = 33.4V$$

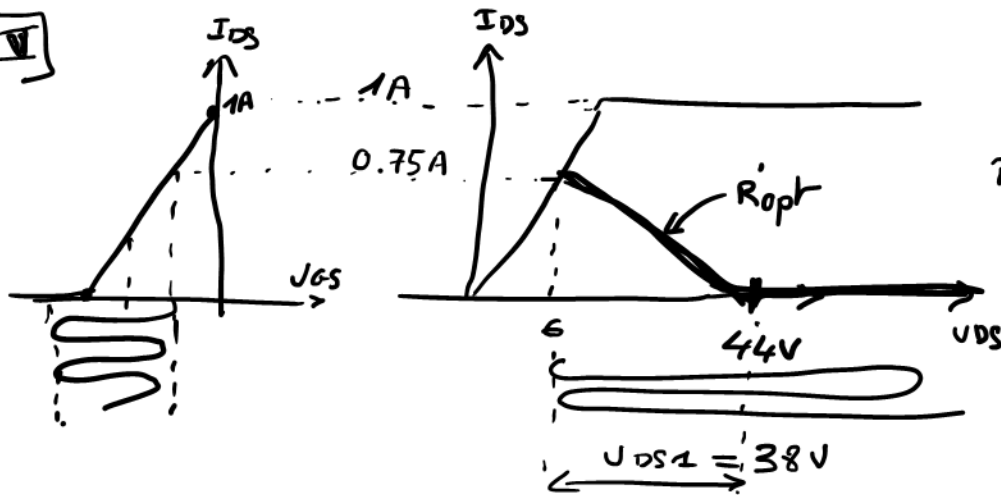
$$P_{out} = \frac{1}{2} V_{DS1} I_{DS1} = 5533 \text{ mW}$$

$$P_{DC} = 305 \text{ mA} \times 33.4V = 10187 \text{ mW}$$

$$PAE = \frac{5533 - 102}{10187} = 53.2\%$$



IV

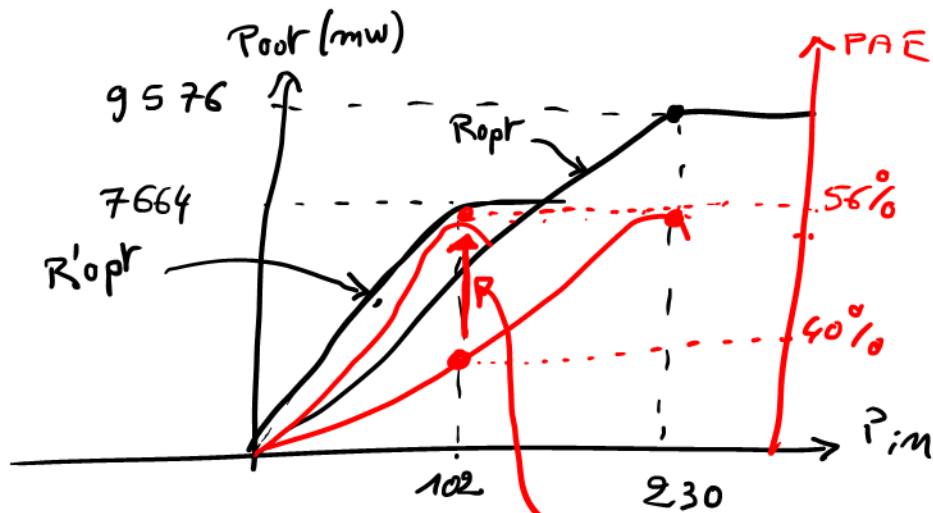


$$P_{out} = \frac{1}{2} \times 38V \times 403 \text{ mA} = 7664 \text{ mW}$$

$$P_{in} = 102 \text{ mW}$$

$$PAE = \frac{7664 - 102}{44 \times 305} = 56\%$$

PAE \nearrow 56% because $V_{DS1} \nearrow$ 38V
40% 27.4V



PAE improvement if $(R_{opt} \rightarrow R'_{opt})$
Principle used in Class B push-pull power amplifiers